



## Product Overview

### PCGA200T65NF8M1: IGBT 650 V, 200 A Field Stop Trench Gen3 (FS3) Bare Die with Solderable Top Metal. Pairing with PCRKA20065F8M1

For complete documentation, see the data sheet.

This 650V Field Stop Trench Gen3 (FS3) IGBT bare die has a die size of 10mm x 10mm. Its emitter pads are covered with Ni/Ag solderable top metal, which enables advanced power module assembly technologies for emitting connection, including Ag Sintering and Cu bare soldering, etc.

#### Features

- AEC-Q101 Qualified
- Maximum Junction Temperature 175°C
- Positive Temperature Coefficient
- Very Low Saturation Voltage:  $V_{CE(SAT)} = 1.53V$  (Typ.) @  $I_C = 200A$
- Short Circuit Rated
- Final Solderable Metal Layer

#### Benefits

- Pass 100% HTRB test which gives better reliability performance than parts passing older version AEC-Q101
- More thermal margin than conventional 150°C rated bare die products
- Easy Paralleling

#### Applications

- Automotive Traction Modules
- General Power Modules

#### End Products

- xEV

### Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	$I_C$ Max (A)	$V_{GE}^{(sa)}$ Typ (V)	$V_F$ Typ (V)	$E_{off}$ Typ (mJ)	$E_{on}$ Typ (mJ)	$T_{rr}$ Typ (ns)	$I_{rr}$ Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand ( $\mu s$ )	$E_{AS}$ Typ (mJ)	$P_D$ Max (W)	Co-Pack aged Diode	Package Type
PCGA200T65NF8M1	AEC Qualified PPAP Capable Pb-free Halide free	NEW														

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